

What is claimed is:

1. A semiconductor integrated circuit device comprising:

a substrate;

5 MOS transistors which are disposed in said substrate and which include gate insulating films; and

an MOS type varactor element which is disposed in said substrate and which includes a gate insulating film, the thickness thereof being thinner than the thinnest gate  
10 insulating film among said gate insulating films of said MOS transistors.

2. A semiconductor integrated circuit device according to Claim 1, wherein a maximum gate voltage applied to said MOS type varactor element is lower than a maximum  
15 gate voltage applied to said MOS transistors.

3. A semiconductor integrated circuit device according to Claim 1, wherein said substrate is a semiconductor substrate.

4. A semiconductor integrated circuit device  
20 according to Claim 2, wherein said substrate is a semiconductor substrate.